

**MMDT5451** 

#### **COMPLEMENTARY NPN / PNP SMALL SIGNAL TRANSISTOR IN SOT363**

#### **Features**

- Epitaxial Planar Die Construction
- Complementary Pair: 1 5551 Type NPN

1 5401 Type PNP

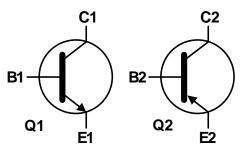
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

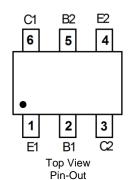
- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)







Device Symbol



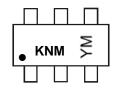
#### **Ordering Information** (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
MMDT5451-7-F	AEC-Q101	KNM	7	8	3,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



KNM = Product Type Marking Code YM = Date Code Marking Y = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Date Code No	<del>-</del> y											
Year	2017	20	18	2019	2020	20	21	2022	2023	20	24	2025
Code	Е	ı	F	G	Н		l	J	K	I	L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Absolute Maximum Ratings – NPN 5551 Section (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	180	V
Collector-Emitter Voltage	V <sub>CEO</sub>	160	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Continuous Collector Current	Ic	200	mA

### Absolute Maximum Ratings - PNP 5401 Section (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-150	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Continuous Collector Current	Ic	-200	mA

#### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Dower Dissination	(Note 5)	Note 5)		mW	
Power Dissipation	(Notes 6 & 7)	$P_D$	320	IIIVV	
Thermal Resistance, Junction to Ambient	(Note 5)	D	625	°C/W	
Thermal Resistance, Junction to Ambient	(Notes 6 & 7)	$R_{\theta JA}$	390		
Thermal Resistance, Junction to Case	(Note 8)	R <sub>θ</sub> JC	140		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

#### Notes:

- 5. For a device mounted on minimum recommended pad layout 1oz weight copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 25mm X 25mm 2oz copper.
- 7. Maximum combined dissipation.
- 8. Thermal resistance from junction to the top of package.



### Electrical Characteristics - NPN 5551 Section (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	180		_	V	$I_C = 100\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	160		_	V	$I_C = 1mA, I_B = 0$	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6			>	$I_E = 10\mu A, I_C = 0$	
Collector-Base Cutoff Current	1			50	nA	$V_{CB} = 120V, I_E = 0$	
Collector-Base Cuton Current	I <sub>CBO</sub>		_	50	μA	$V_{CB} = 120V, I_E = 0, T_A = +100$ °C	
Base-Emitter Cutoff Current	I <sub>EBO</sub>		_	50	nA	$V_{EB} = 4V, I_C = 0$	
ON CHARACTERISTICS (Note 9)							
		80				$I_C = 1.0$ mA, $V_{CE} = 5.0$ V	
DC Current Gain	h <sub>FE</sub>	80	_	250	_	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 5.0V	
		30		_		I <sub>C</sub> = 50mA, V <sub>CE</sub> = 5.0V	
Collector-Emitter Saturation Voltage	.,			0.15	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA	
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		_	0.20	V	$I_C = 50mA$ , $I_B = 5.0mA$	
Base-Emitter Saturation Voltage	V		_	1.0	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 1.0mA	
Base-Emilier Saturation voltage	$V_{BE(SAT)}$					$I_C = 50 \text{mA}, I_B = 5.0 \text{mA}$	
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C <sub>obo</sub>	_		6.0	pF	$V_{CB} = 10V$ , $f = 1.0MHz$ , $I_E = 0$	
Small Signal Current Gain	h <sub>fe</sub>	50		250	_	$I_C = 1mA, V_{CE} = 10V, f = 1.0MHz$	
Current Gain-Bandwidth Product	f <sub>T</sub>	100		300	MHz	$I_C = 10$ mA, $V_{CE} = 10$ V, $f = 100$ MHz	
Noise Figure	NF	_	_	8.0	dB	$V_{CE} = 5.0V, I_{C} = 200\mu A,$ $R_{S} = 1k\Omega, f = 1.0kHz$	

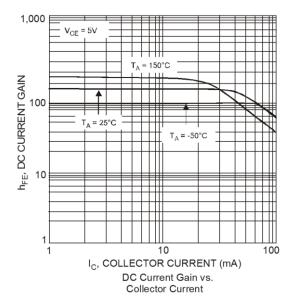
## Electrical Characteristics - PNP 5401 Section (@TA = +25°C, unless otherwise specified.)

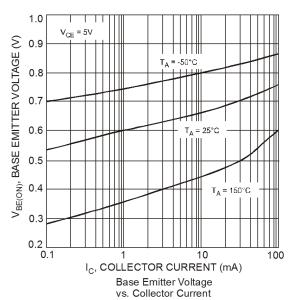
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS								
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-160			V	$I_C = -100\mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-150	_	_	V	$I_C = -1 \text{mA}, I_B = 0$		
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6	_	_	V	$I_E = -10\mu A, I_C = 0$		
Collector-Base Cutoff Current	1	_	_	-50	nA	V <sub>CB</sub> = -120V, I <sub>E</sub> = 0		
Collector-base Cuton Current	I <sub>CBO</sub>	_	_	-50	μΑ	V <sub>CB</sub> = -120V, I <sub>E</sub> = 0, T <sub>A</sub> = +100°C		
Base-Emitter Cutoff Current	I <sub>EBO</sub>	_	_	-50	nA	V <sub>EB</sub> = -4V, I <sub>C</sub> = 0		
ON CHARACTERISTICS (Note 9)	ON CHARACTERISTICS (Note 9)							
		50				$I_C = -1.0 \text{mA}, V_{CE} = -5.0 \text{V}$		
DC Current Gain	h <sub>FE</sub>	60	_	240	_	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -5.0V		
		50		_		$I_C = -50 \text{mA}, V_{CE} = -5.0 \text{V}$		
Collector Emitter Seturation Voltage	\/			-0.20	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA		
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (SAT)	_	_	-0.50	V	$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$		
Door Emitter Coturation Voltage	.,			1.0	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA		
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_		-1.0		I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA		
SMALL SIGNAL CHARACTERISTICS								
Output Capacitance	C <sub>obo</sub>	_		6.0	pF	$V_{CB} = -10V$ , $f = 1.0MHz$ , $I_E = 0$		
Small Signal Current Gain	h <sub>fe</sub>	40	_	260		$I_C = -1mA$ , $V_{CE} = -10V$ , $f = 1.0MHz$		
Current Gain-Bandwidth Product	f <sub>T</sub>	100		300	MHz	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -10V, f = 100MHz		
Noise Figure	NF		_	8.0	dB	$V_{CE} = -5.0V$ , $I_{C} = -200\mu A$ , $R_{S} = 1\Omega$ , $f = 1.0kHz$		

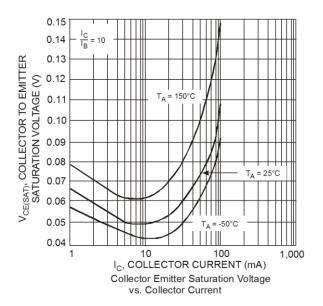
Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.

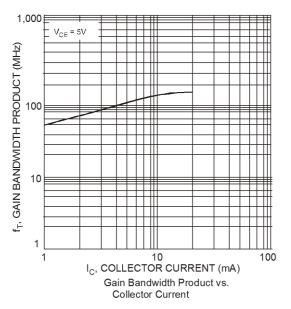


### Typical Electrical Characteristics - NPN 5551 Section (@TA = +25°C, unless otherwise specified.)





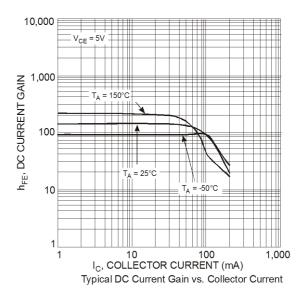


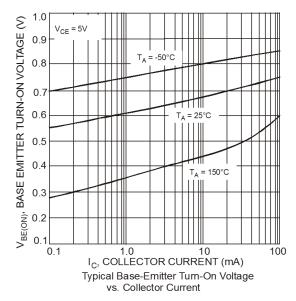


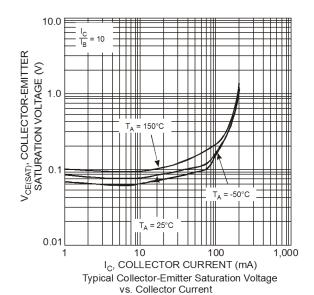
June 2018

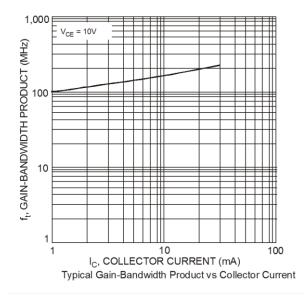


### Typical Electrical Characteristics - PNP 5401 Section (@TA = +25°C, unless otherwise specified.)







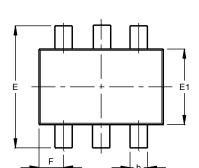


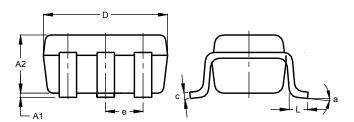
June 2018



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.





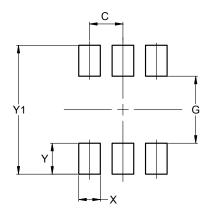
SOT363							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.10	0.30	0.25				
С	0.10	0.22	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	0.650 BSC						
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### **SOT363**

**SOT363** 



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Υ	0.600
V1	2 500

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking. Note:



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